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Messrs. Rockwell Automation

捷多邦，专业PCB打样工厂，24小时加急出货

SPECIFICATION

Device Name : IGBT Module

Type Name : 7MBR35SB140-01

Spec. No. : MS6M 0556

Date : Jun. - 02 - 2000

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Fuji Electric Co., Ltd.
Matsumoto Factory

DATE		NAME		APPROVED	Fuji Electric Co.,Ltd.						
DRAWN	Jun. - 2 - '00	Y. Kobayashi		J. Miyazaki	DWG. NO.	MS6M 0556	1 / 10	<table><tr><td>α</td></tr><tr><td></td></tr><tr><td></td></tr></table>	α		
α											
CHECKED	June - 2 - '00	S. Kato									
dzsc.com											

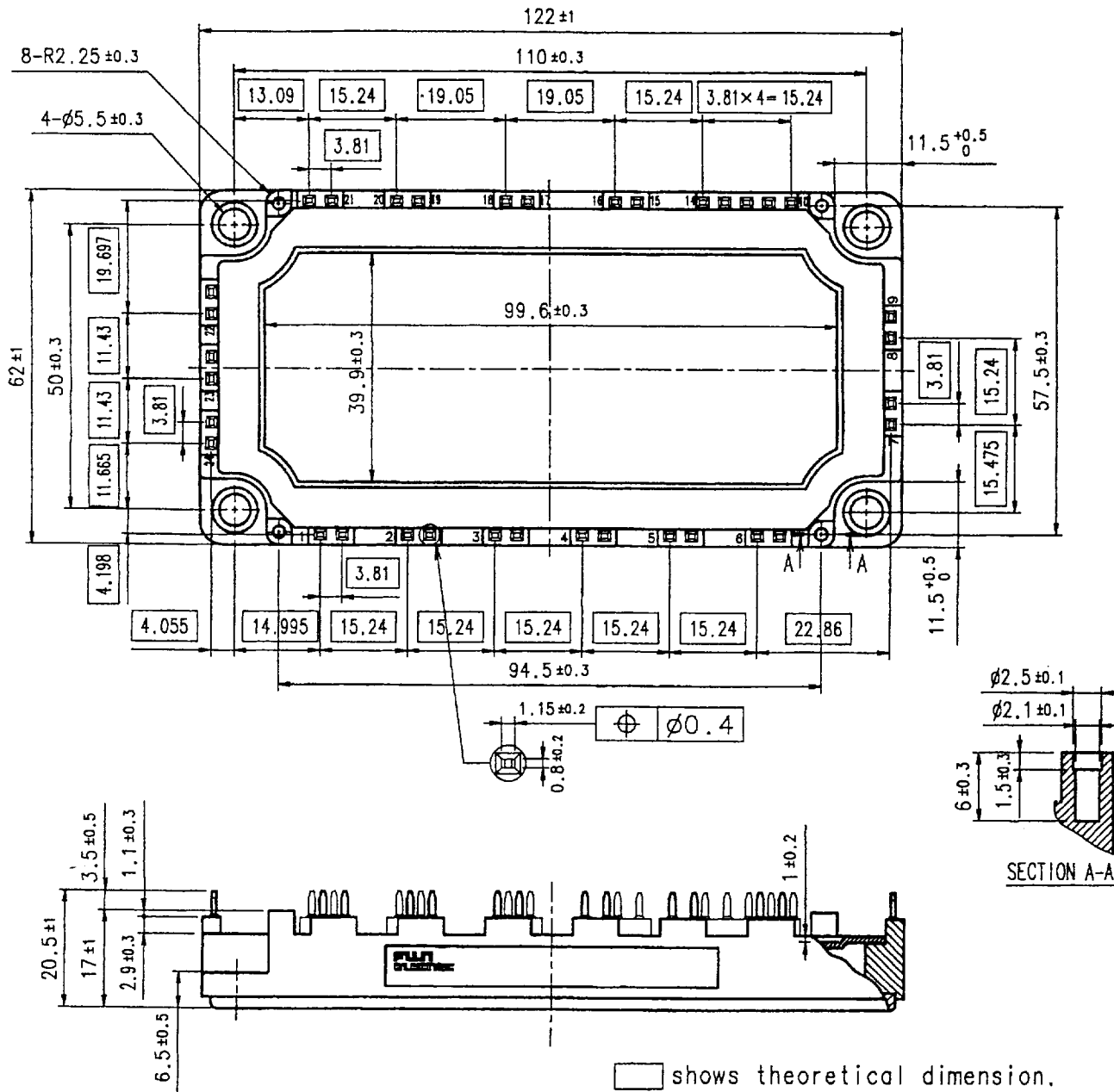
Revised Records

Date	Classi- fication	Ind.	Content	Applied date	Drawn	Checked	Approved
Jun.-2-'60	enactment	—	—	Issued date	—	S. Miyata	T. Miyatake
Jun.-14-'60	Revision	a	Revised type wiss (P5/10)		T. Kikiguchi	S. Miyata	T. Miyatake

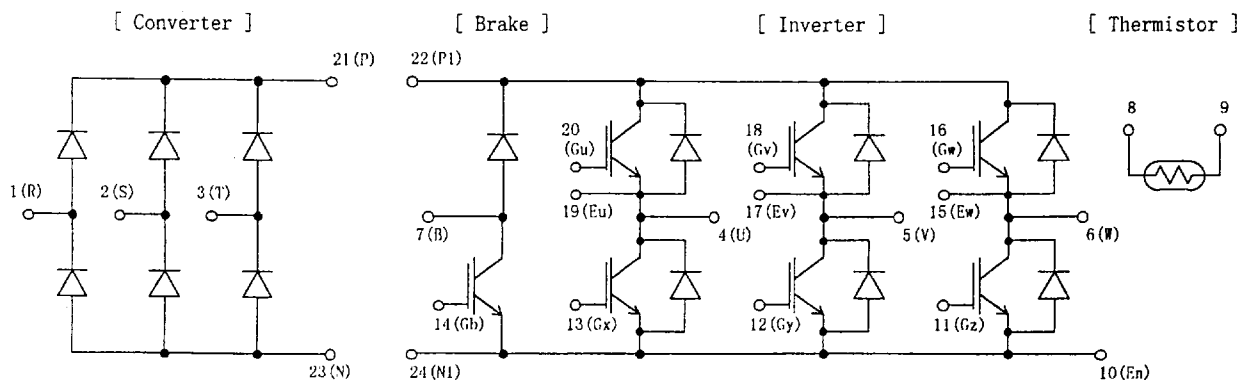
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7MBR35SB140-01

1. Outline Drawing (Unit : mm)



2. Equivalent circuit



3. Absolute Maximum Ratings (at Tc= 25C unless otherwise specified)

Items		Symbols	Conditions		Maximum Ratings	Units
Inverter	Collector-Emitter voltage	VCES			1400	V
	Gate-Emitter voltage	VGES			+20	V
	Collector current	Ic	Continuous	Tc=25C	50	A
				Tc=75C	35	
		Icp	1ms	Tc=25C	100	A
				Tc=75C	70	
		-Ic			35	A
Collector Power Dissipation	Pc	1 device		240	W	
Brake	Collector-Emitter voltage	VCES			1400	V
	Gate-Emitter voltage	VGES			+20	V
	Collector current	Ic	Continuous	Tc=25C	35	A
				Tc=75C	25	
		Icp	1ms	Tc=25C	70	A
				Tc=75C	50	
	Collector Power Dissipation	Pc	1 device		180	W
Repetitive peak reverse Voltage(Diode)	VRRM			1400	V	
Converter	Repetitive peak reverse Voltage	VRRM			1600	V
	Average Output Current	Io	50Hz/60Hz sine wave		35	A
	Surge Current (Non-Repetitive)	IFSM	Tj=150C,10ms		360	A
	I ² t (Non-Repetitive)	I ² t	half sine wave		648	A ² s
	Junction temperature	Tj			150	C
Storage temperature		Tstg			-40~ +125	C
Isolation voltage	between terminal and copper base ^{(*)1}	Viso	AC : 1min.		2500	V
	between thermistor and others ^{(*)2}				2500	V
Mounting Screw Torque ^{(*)3}					3.5	Nm

(*)1 All terminals should be connected together when isolation test will be done.

(*)2 Terminal 8 and 9 should be connected together. Terminal 1 to 7 and 10 to 24 should be connected together and shorted to copper base.

(*)3 Recommendable Value : 2.5~3.5 Nm (M5)

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4. Electrical characteristics (at Tj= 25C unless otherwise specified)

	Items	Symbols	Conditions	Characteristics			Units
				min.	typ.	Max.	
Inverter	Zero gate voltage Collector current	ICES	VGE = 0 V, VCE ^② 1400 V			1.0	mA
	Gate-Emitter leakage current	IGES	VCE = 0 V, VGE = +20 V			200	nA
	Gate-Emitter threshold voltage	VGE(th)	VCE = 20 V, Ic = 35 mA	5.5	7.2	8.5	V
	Collector-Emitter saturation voltage	VCE(sat)	VGE = 15 V, chip		2.2		V
			Ic = 35 A terminal		2.35	2.7	
	Input capacitance	Cies	VGE = 0 V, VCE = 10 V f = 1 MHz		4200		pF
	Turn-on time	ton	Vcc= 800 V		0.35	1.2	us
		tr	Ic = 35 A		0.25	0.6	
		tr(0)	VGE = +15 V		0.1		
	Turn-off time	toff	RG = 33 ohm		0.45	1.0	
		tf			0.08	0.3	
Brake	Forward on voltage	VF	IF = 35 A chip		2.4		V
			terminal		2.55	3.4	
	Reverse recovery time	trr	IF = 35 A			350	ns
	Zero gate voltage Collector current	ICES	VGE = 0 V, VCE ^② 1400 V			1.0	mA
	Gate-Emitter leakage current	IGES	VCE = 0 V, VGE = +20 V			200	nA
	Collector-Emitter saturation voltage	VCE(sat)	VGE = 15 V, chip		2.2		V
			Ic = 25 A terminal		2.35	2.8	
	Turn-on time	ton	Vcc= 800 V		0.35	1.2	us
		tr	Ic = 25 A		0.25	0.6	
	Turn-off time	toff	VGE = +15 V		0.45	1.0	
		tf	RG = 51 ohm		0.08	0.3	
Converter	Reverse current	IRRM	VR = 1400 V			1.0	mA
	Forward on voltage	VFM	IF = 35 A chip		1.1		V
			terminal		1.2	1.5	
Thermistor	Reverse current	IRRM	VR = 1600 V			1.0	mA
	Resistance	R	T = 25C		5000		ohm
			T = 100C	465	495	520	
	B value	B	T = 25/50C	3305	3375	3450	K

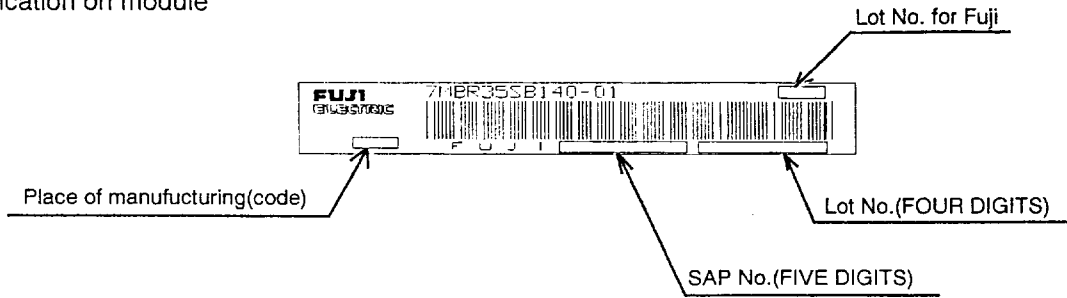
5. Thermal resistance characteristics

Items	Symbols	Conditions	Characteristics			Units
			min.	typ.	Max.	
Thermal resistance (1 device)	Rth(j-c)	Inverter IGBT			0.52	C/W
		Inverter FWD			0.90	
		Brake IGBT			0.69	
		Converter Diode			0.75	
Contact Thermal resistance	Rth(c-f)	with Thermal Compound (*)		0.05		C/W

* This is the value which is defined mounting on the additional cooling fin with thermal compound.

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6. Indication on module



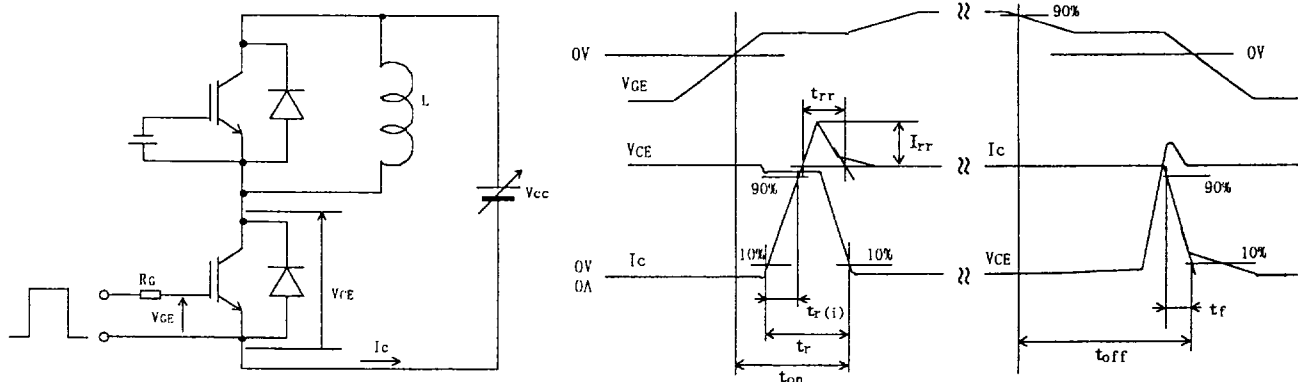
7. Applicable category

This specification is applied to Power Integrated Module named 7MBR35SB140-01 .

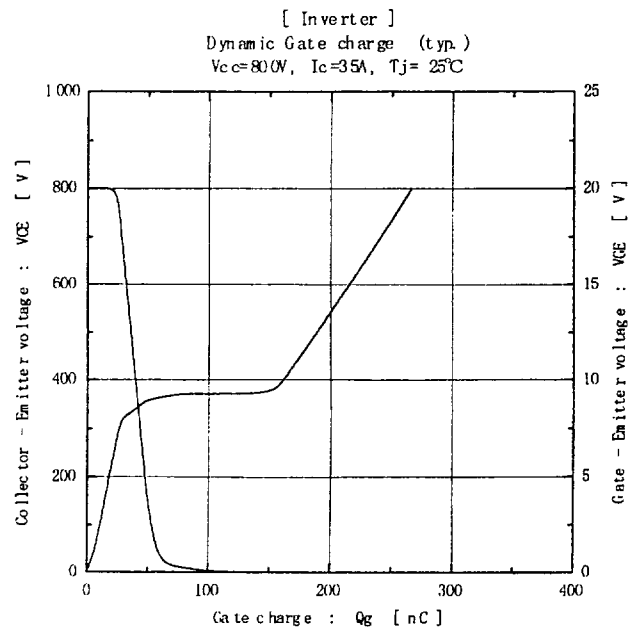
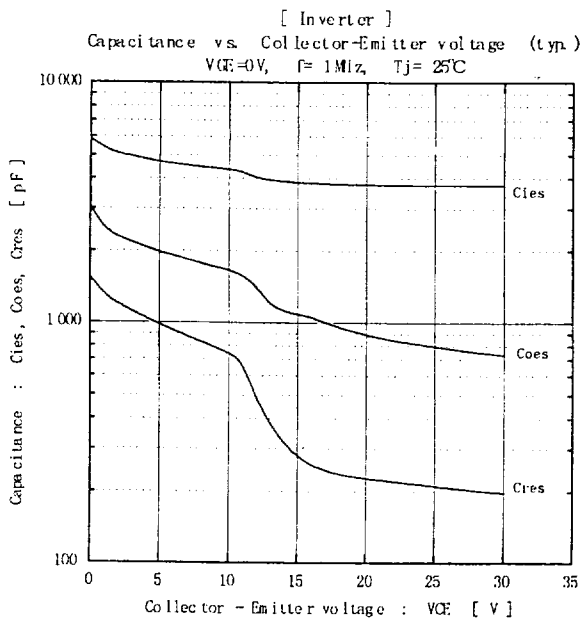
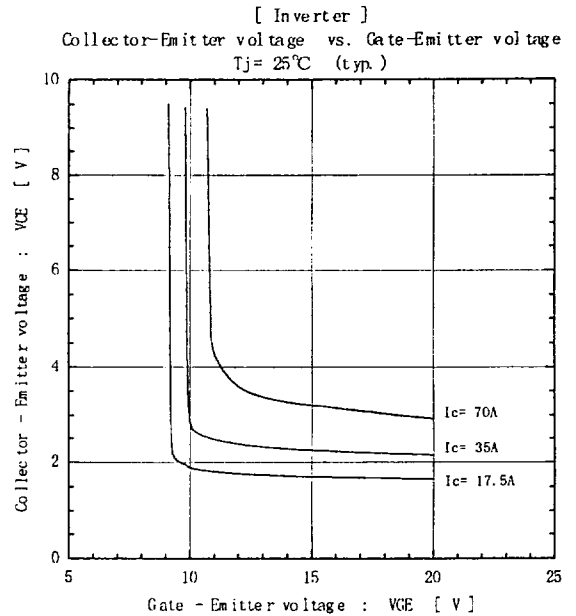
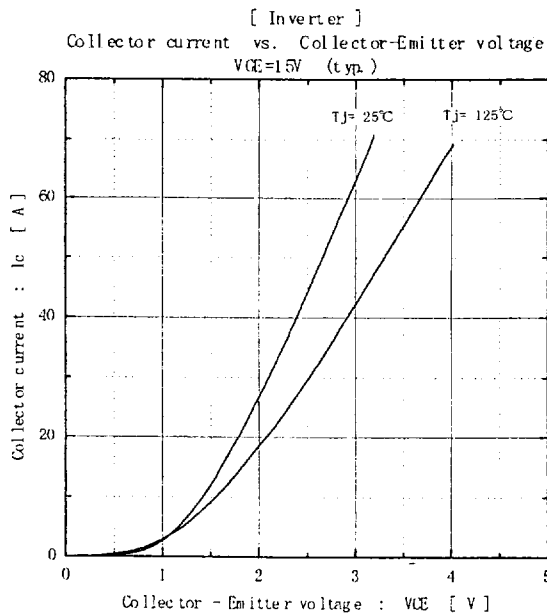
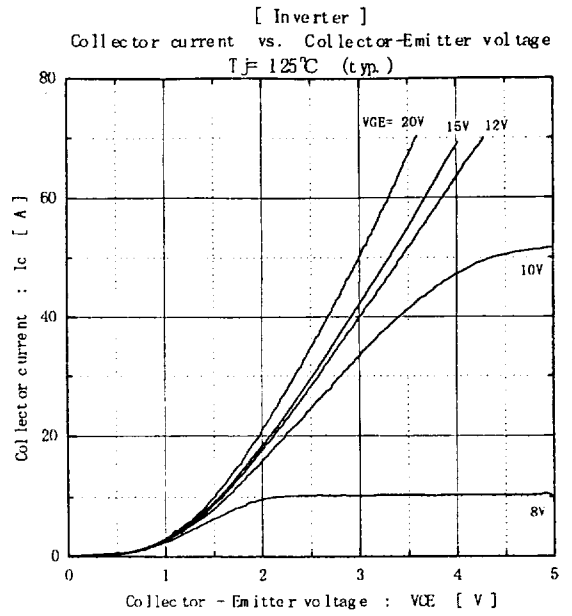
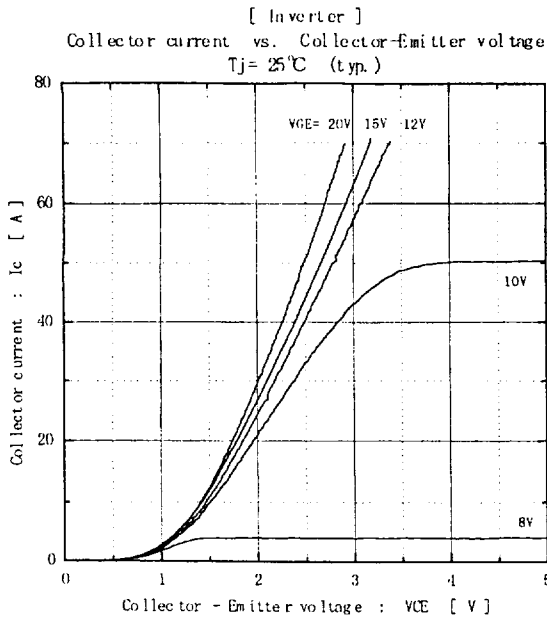
8. Storage and transportation notes

- The module should be stored at a standard temperature of 5 to 35°C and humidity of 45 to 75% .
- Store modules in a place with few temperature changes in order to avoid condensation on the module surface.
- Avoid exposure to corrosive gases and dust.
- Avoid excessive external force on the module.
- Store modules with unprocessed terminals.
- Do not drop or otherwise shock the modules when transporting.
- Please connect adequate fuse or protector of circuit between three-phase line and this product to prevent the equipment from causing secondary destruction.

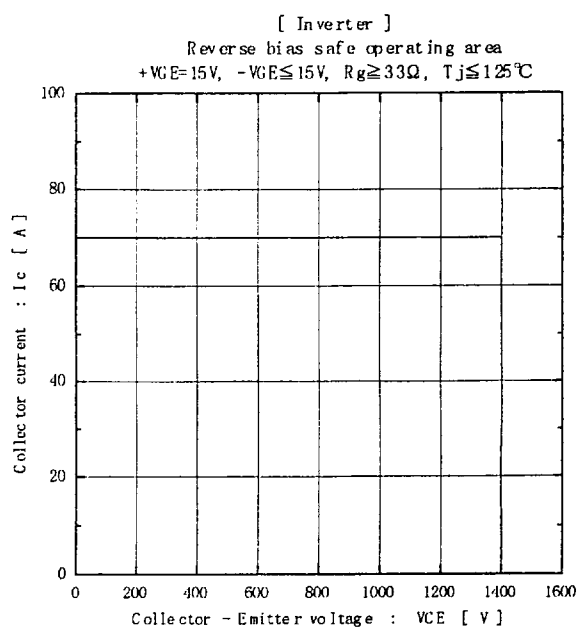
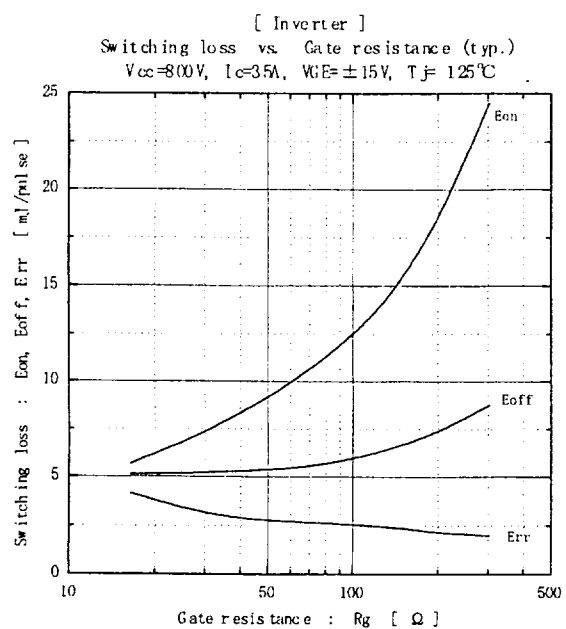
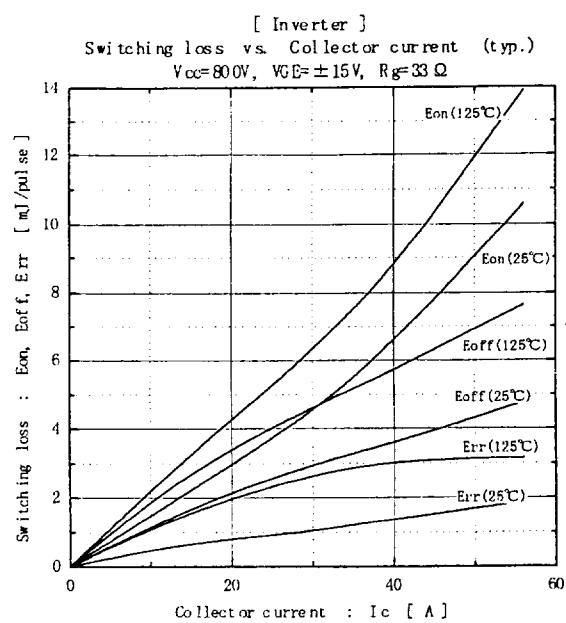
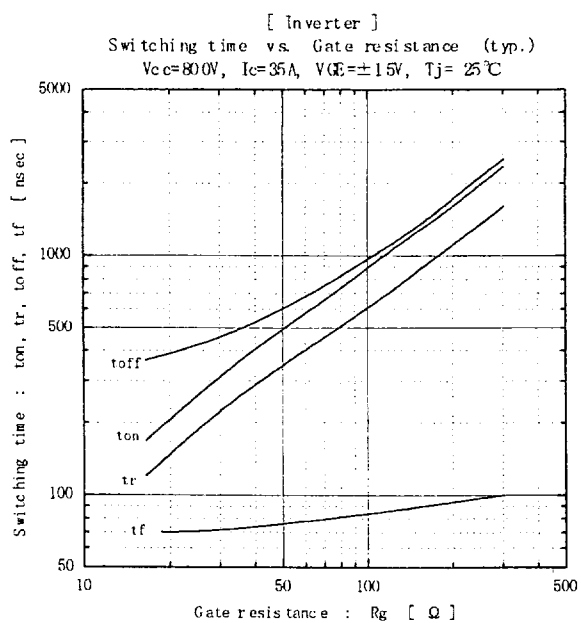
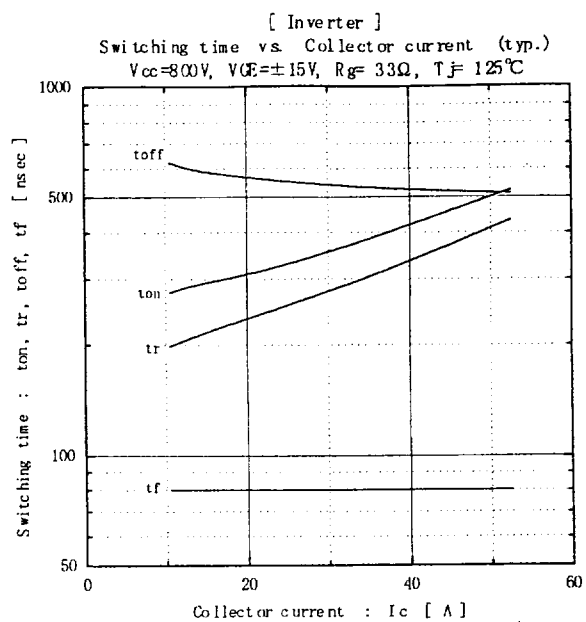
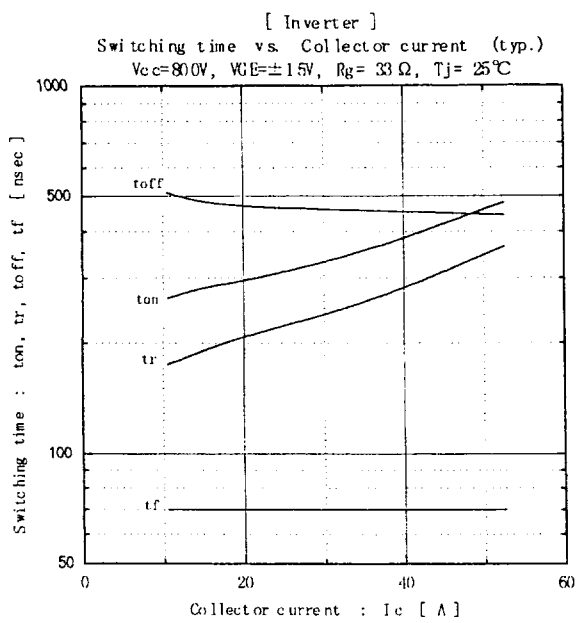
9. Definitions of switching time



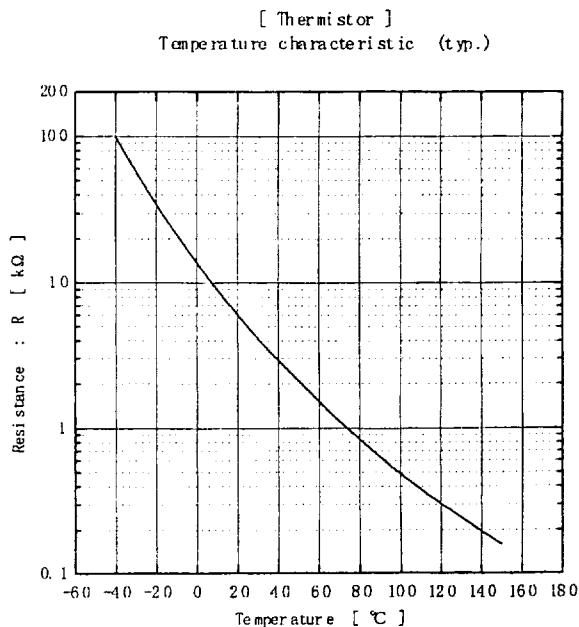
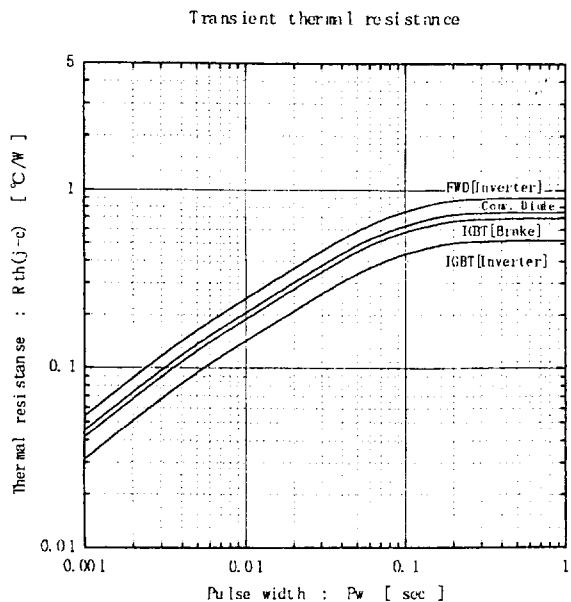
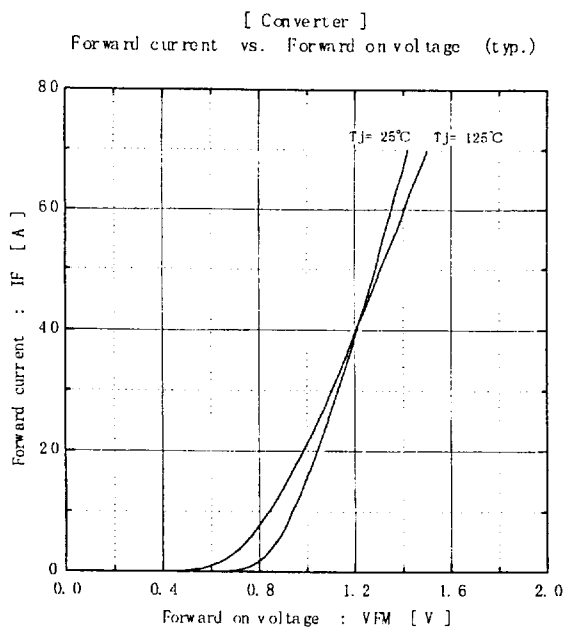
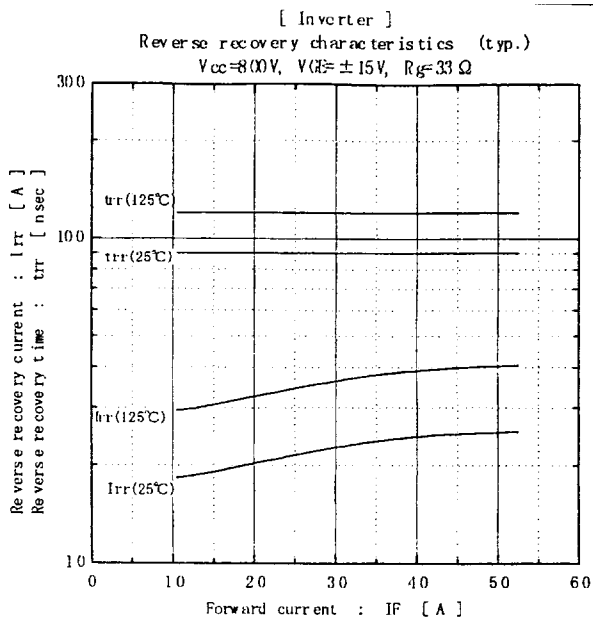
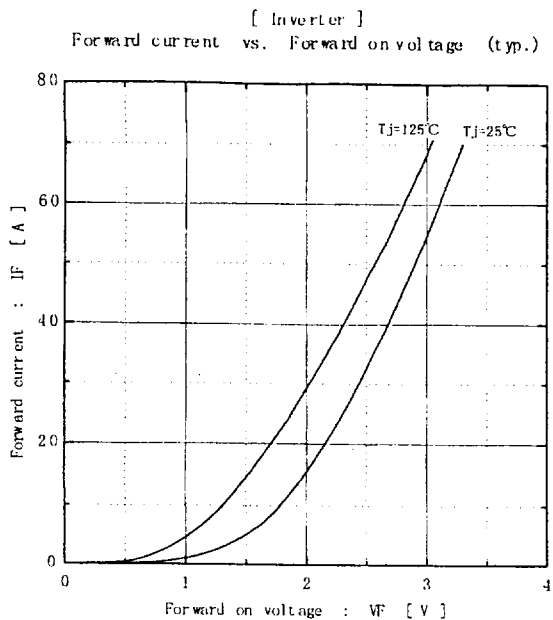
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